Lonten N-channel 500V, 18A Power MOSFET

Description

The Power MOSFET is fabricated using the advanced planar VDMOS technology. The resulting device has low conduction resistance, superior switching performance and high avalanche energy.

Features

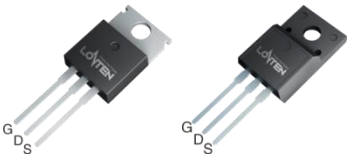
- Low $R_{DS(on)}$
- Low gate charge (typ. Q_g =50.5 nC)
- 100% UIS tested
- RoHS compliant

Applications

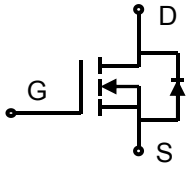
- Electronic ballast
- Switched mode power supplies.
- UPS.

Product Summary

V_{DSS}	500V
I_D	18A
$R_{DS(on),max}$	0.28Ω
$Q_{g,typ}$	50.5 nC



TO-220 **TO-220F**



N-Channel MOSFET

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	500	V
Continuous drain current (T_C = 25°C)	I_D	18	A
(T_C = 100°C)		11.4	A
Pulsed drain current [1]	I_{DM}	72	A
Gate-Source voltage	V_{GSS}	±30	V
Avalanche energy, single pulse [2]	E_{AS}	810	mJ
Peak diode recovery dv/dt [3]	dv/dt	5	V/ns
Power Dissipation TO-220F (T_C = 25°C)	P_D	54	W
Derate above 25°C		0.43	W/°C
Power Dissipation TO-220 (T_C = 25°C)		232	W
Derate above 25°C		1.86	W/°C
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150	°C
Continuous diode forward current	I_S	18	A
Diode pulse current	$I_{S,pulse}$	72	A

Thermal Characteristics

Parameter	Symbol	Value		Unit
		TO-220F	TO-220	
Thermal resistance, Junction-to-case	$R_{\theta JC}$	2.31	0.54	°C/W
Thermal resistance, Junction-to-ambient	$R_{\theta JA}$	62.5	62.5	°C/W

Package Marking and Ordering Information

Device	Device Package	Marking	Units/Tube	Units/Real
LNC18N50	TO-220	LNC18N50	50	
LND18N50	TO-220F	LND18N50	50	

Electrical Characteristics

T_c = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0 V, I_D=0.25 mA	500	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=0.25 mA	2	-	4	V
Drain cut-off current	I_{DSS}	V_{DS}=500 V, V_{GS}=0 V, T_j = 25°C T_j = 125°C	 - -	 -	 1 100	 μA
Gate leakage current, Forward	I_{GSSF}	V_{GS}=30 V, V_{DS}=0 V	-	-	100	nA
Gate leakage current, Reverse	I_{GSSR}	V_{GS}=-30 V, V_{DS}=0 V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=9 A	-	0.24	0.28	Ω
Dynamic characteristics						
Input capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	-	3045	-	pF
Output capacitance	C_{oss}		-	284	-	
Reverse transfer capacitance	C_{rss}		-	12	-	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 250 V, I_D = 18 A R_G = 10 Ω, V_{GS}=15 V	-	17.5	-	ns
Rise time	t_r		-	42	-	
Turn-off delay time	$t_{d(off)}$		-	101	-	
Fall time	t_f		-	15.5	-	
Gate charge characteristics						
Gate to source charge	Q_{gs}	V_{DD}=400 V, I_D=18 A, V_{GS}=0 to 10 V	-	12.7	-	nC
Gate to drain charge	Q_{gd}		-	15.8	-	
Gate charge total	Q_g		-	50.5	-	
Gate plateau voltage	$V_{plateau}$		-	5	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=18 A	-	-	1.3	V
Reverse recovery time	t_{rr}	V_R=400 V, I_F=18 A, dI_F/dt=100 A/μs	-	368	-	ns
Reverse recovery charge	Q_{rr}		-	4.6	-	μC
Peak reverse recovery current	I_{rrm}		-	25	-	A

Notes:

1. Pulse width limited by maximum junction temperature.
2. L=5mH, I_{AS} = 18A, Starting T_j= 25°C.
3. I_{SD} = 18A, di/dt≤100A/us, V_{DD}≤BV_{DS}, Starting T_j= 25°C.

Electrical Characteristics Diagrams

Figure 1. Typical Output Characteristics

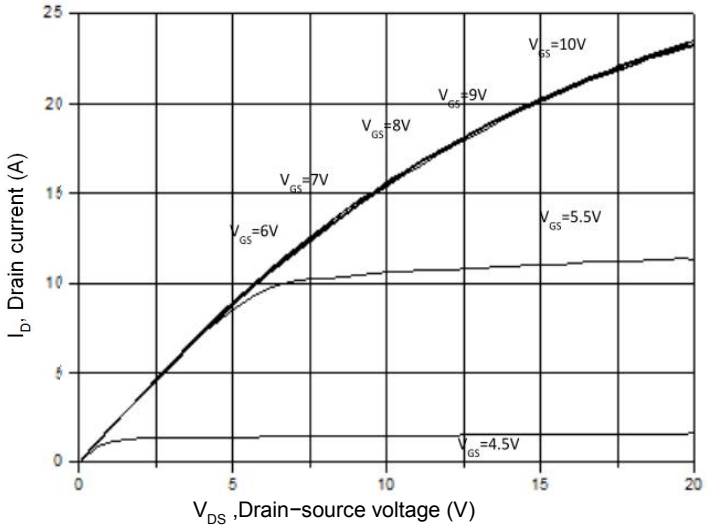


Figure 2. Transfer Characteristics

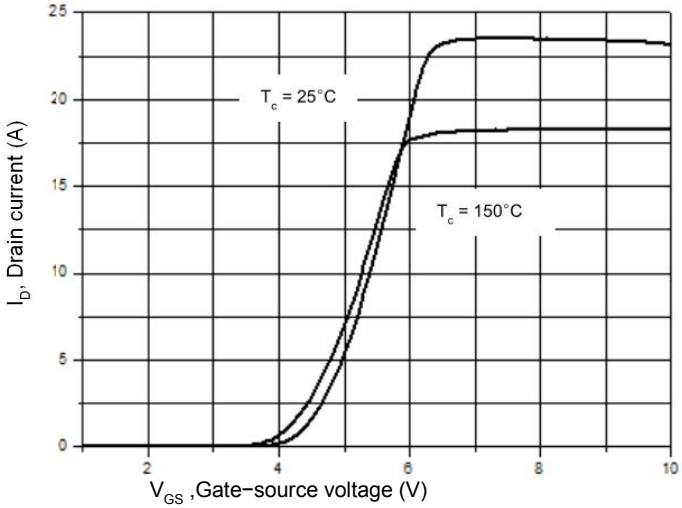


Figure 3. On-Resistance Variation vs. Drain Current

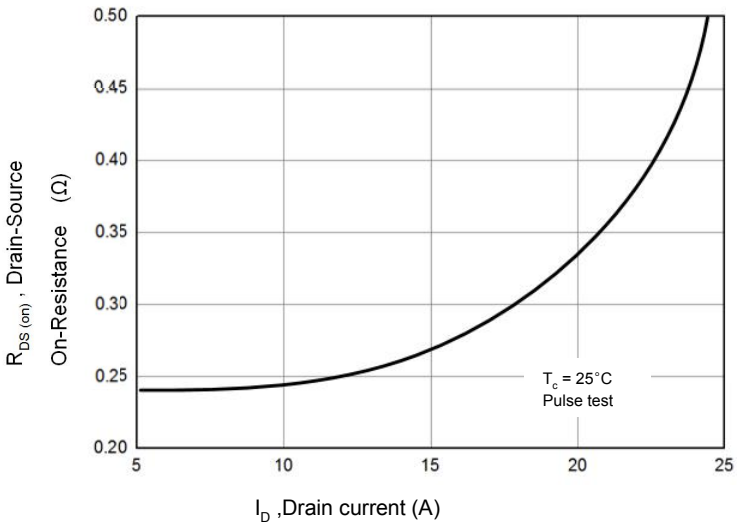


Figure 4. Threshold Voltage vs. Temperature

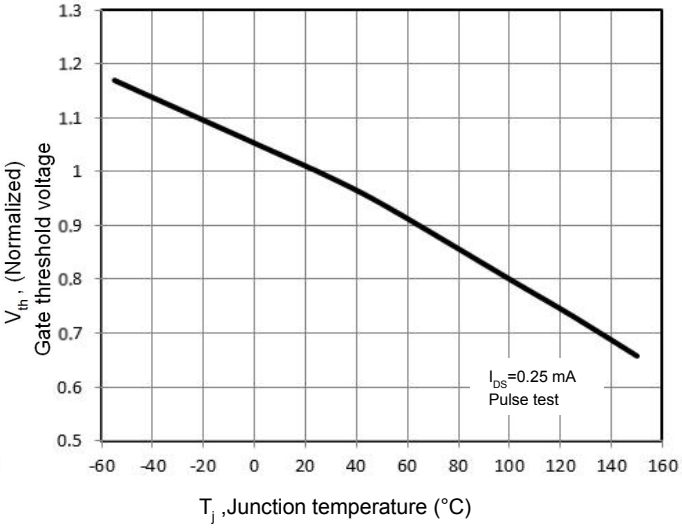


Figure 5. Breakdown Voltage vs. Temperature

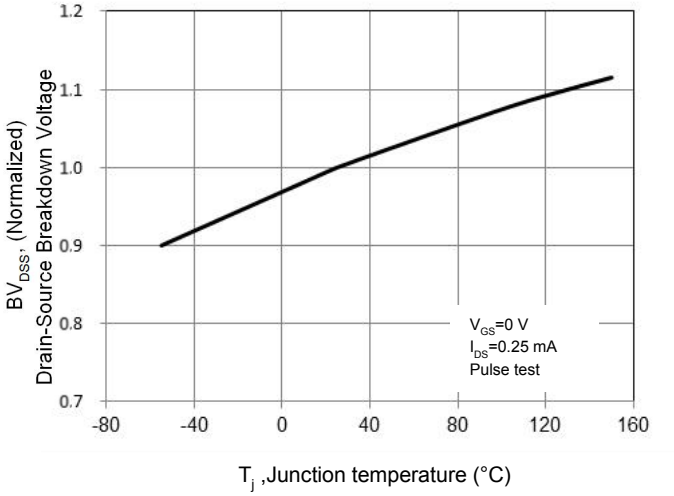


Figure 6. On-Resistance vs. Temperature

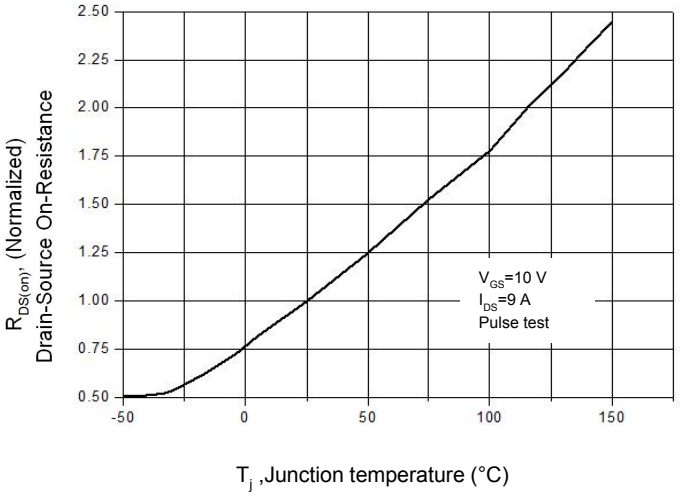


Figure 7. Capacitance Characteristics

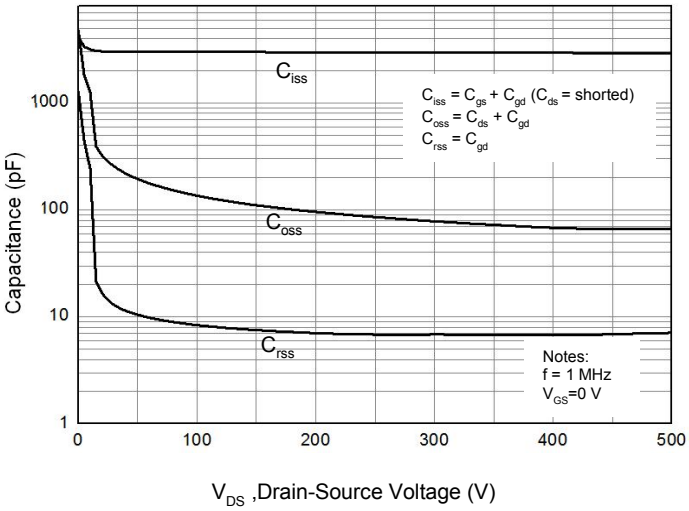


Figure 8. Gate Charge Characteristics

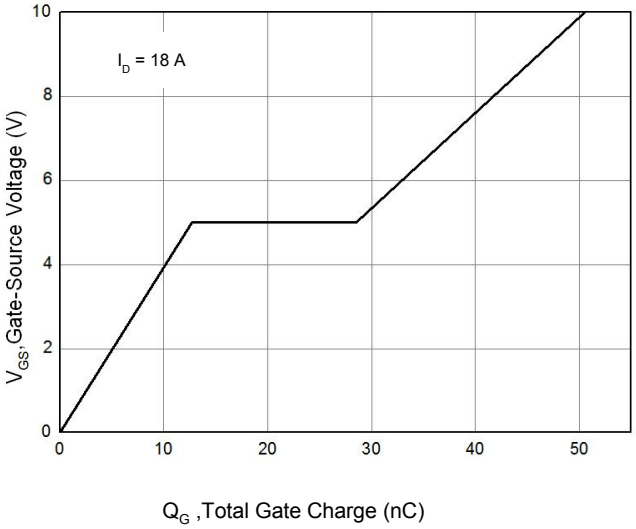


Figure 9. Maximum Safe Operating Area

TO-220F

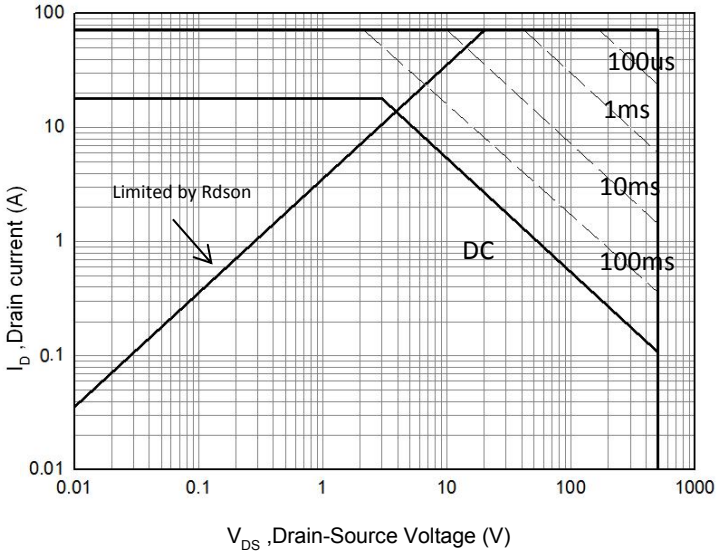


Figure 10. Maximum Safe Operating Area

TO-220

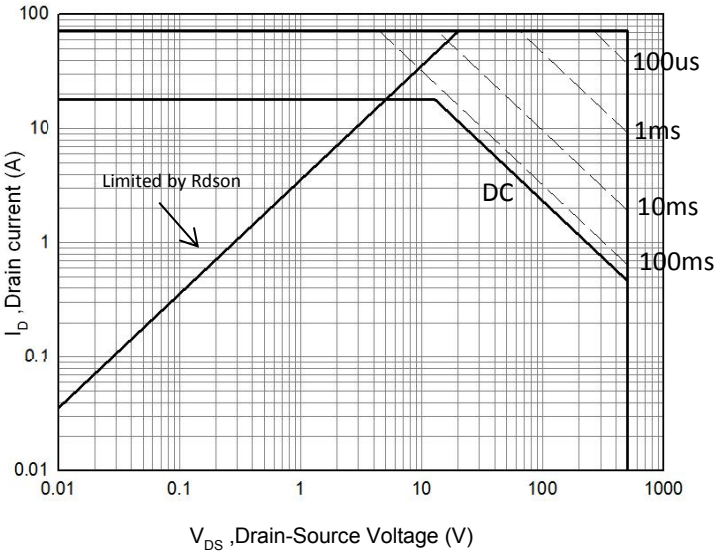


Figure 11. Power Dissipation vs. Temperature

TO-220F

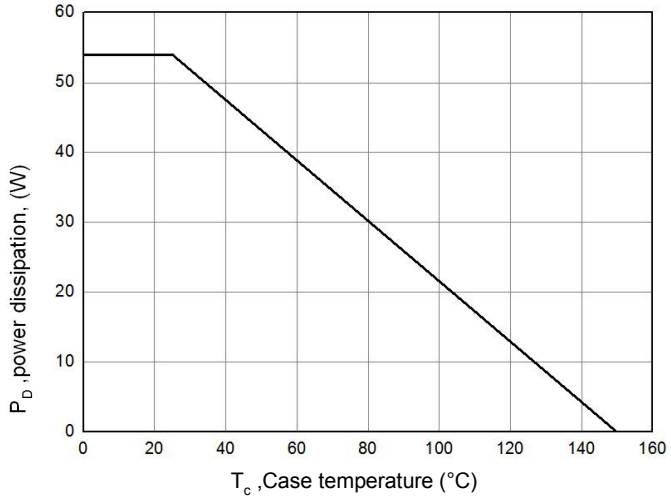


Figure 12. Power Dissipation vs. Temperature

TO-220

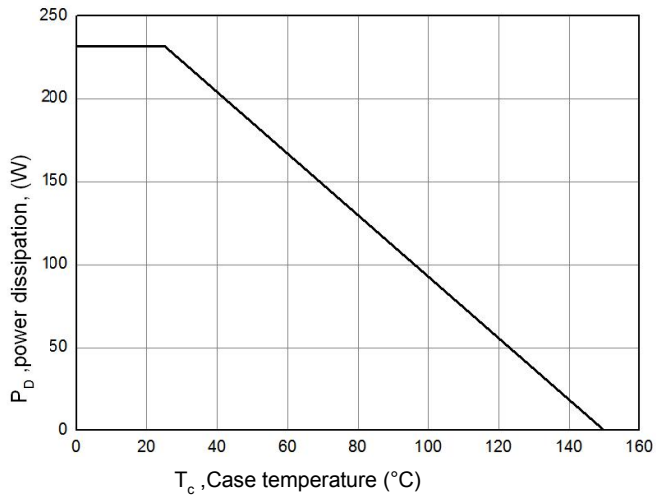


Figure 13. Continuous Drain Current vs. Temperature

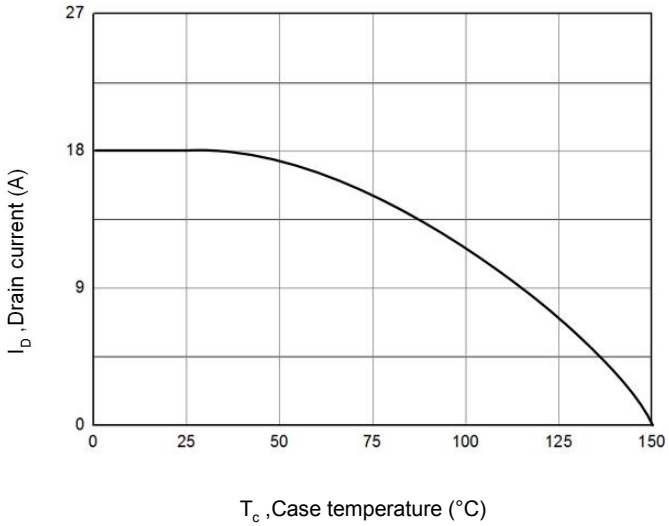


Figure 14. Body Diode Transfer Characteristics

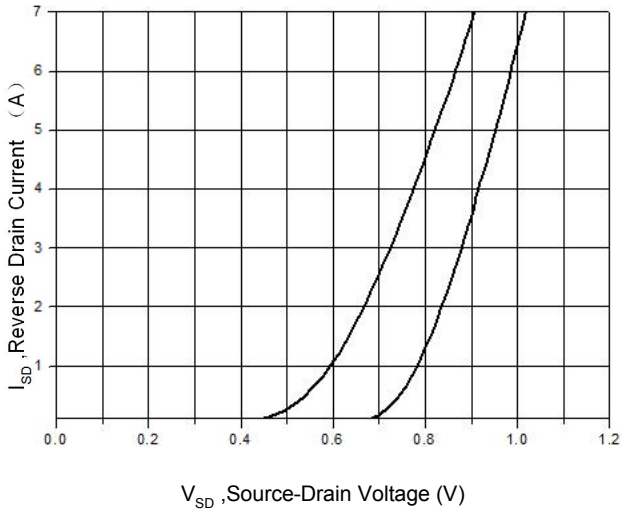


Figure 15 Transient Thermal Impedance, Junction to Case, TO-220F

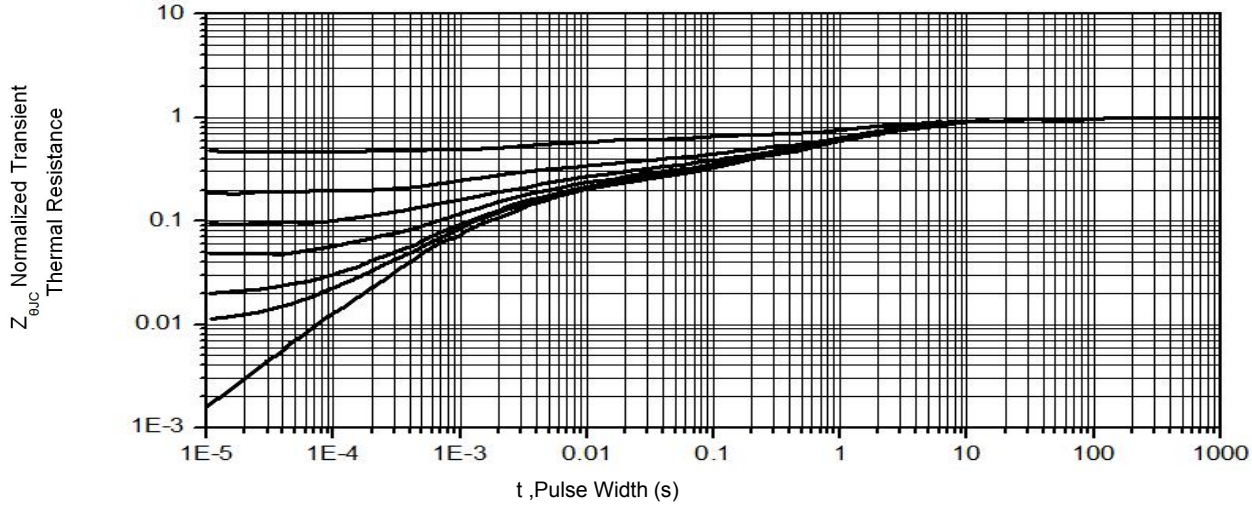
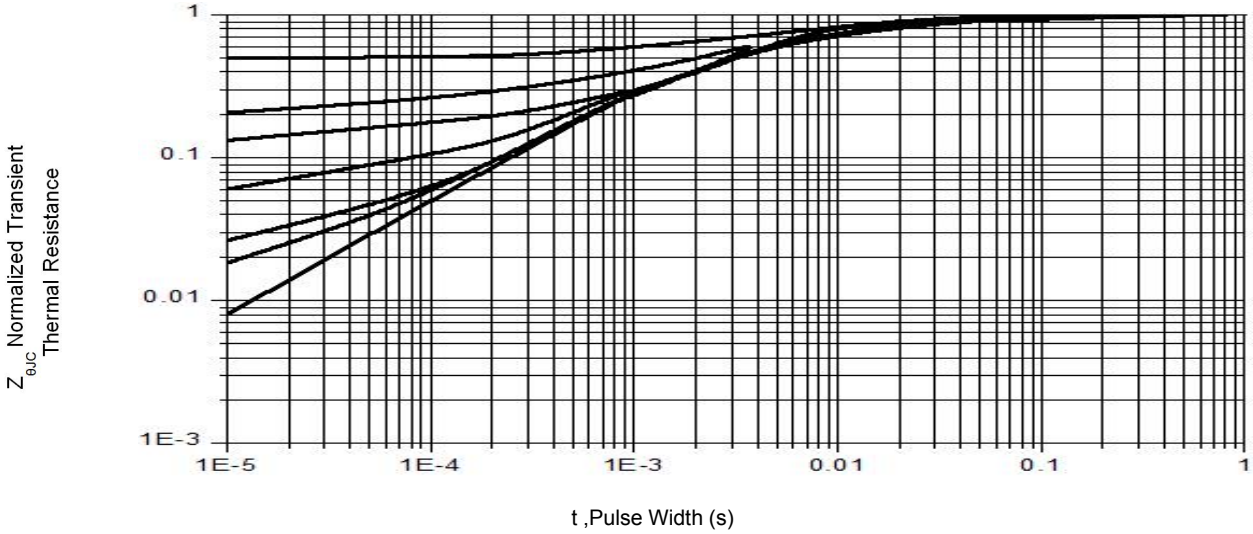
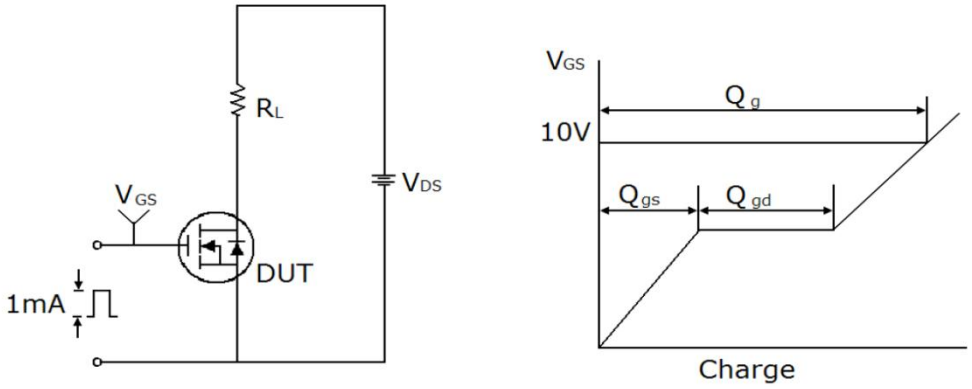


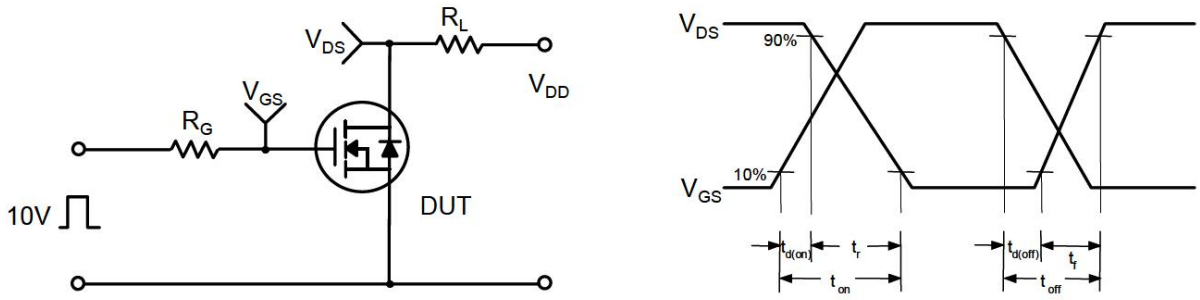
Figure 16. Transient Thermal Impedance, Junction to Case, TO-220



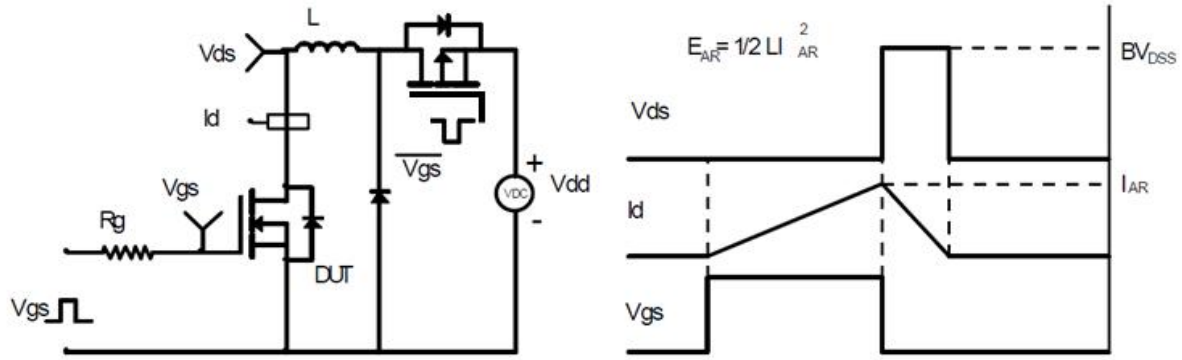
Gate Charge Test Circuit & Waveform



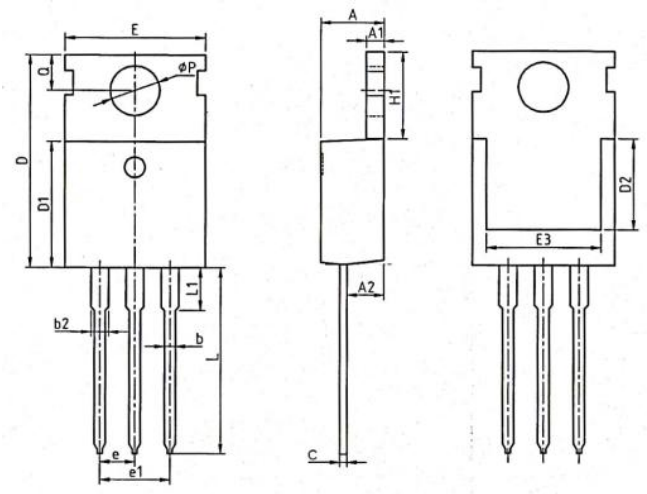
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

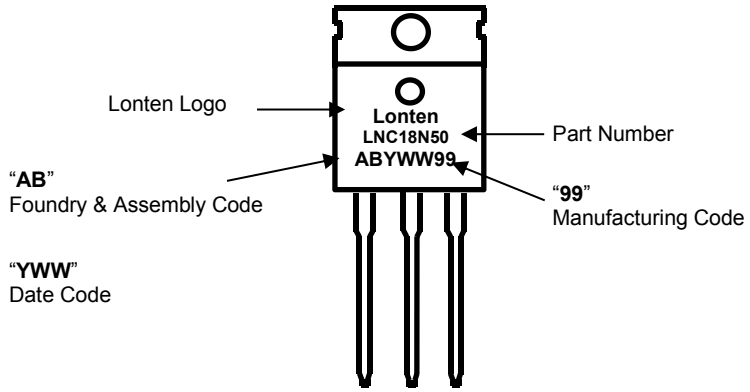


Mechanical Dimensions for TO-220

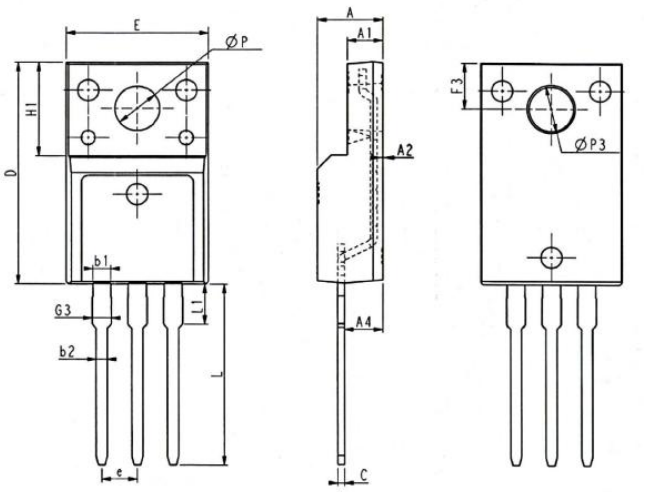


COMMON DIMENSIONS						
SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.37	4.57	4.70	0.172	0.180	0.185
A1	1.25	1.30	1.40	0.049	0.051	0.055
A2	2.20	2.40	2.60	0.087	0.094	0.102
b	0.70	0.80	0.95	0.028	0.031	0.037
b2	1.17	1.27	1.47	0.046	0.050	0.058
c	0.45	0.50	0.60	0.018	0.020	0.024
D	15.10	15.60	16.10	0.594	0.614	0.634
D1	8.80	9.10	9.40	0.346	0.358	0.370
D2	5.50	—	—	0.217	—	—
E	9.70	10.00	10.30	0.382	0.394	0.406
E3	7.00	—	—	0.276	—	—
e	2.54BSC			0.1BSC		
e1	5.08BSC			0.2BSC		
H1	6.25	6.50	6.85	0.246	0.256	0.270
L	12.75	13.50	13.80	0.502	0.531	0.543
L1	—	3.10	3.40	—	0.122	0.134
Øp	3.40	3.60	3.80	0.134	0.142	0.150
Q	2.60	2.80	3.00	0.102	0.110	0.118

TO-220 Part Marking Information

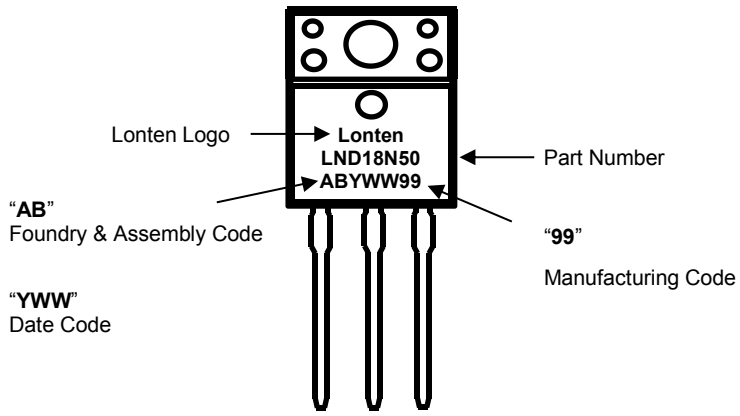


Mechanical Dimensions for TO-220F



COMMON DIMENSIONS						
SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NO	MA
E	9.96	10.1	10.3	0.39	0.40	0.40
A	4.50	4.70	4.90	0.17	0.18	0.19
A1	2.34	2.54	2.74	0.09	0.10	0.10
A2	0.30	0.45	0.60	0.01	0.00	0.02
A4	2.65	2.76	2.96	0.10	0.10	0.11
C	0.40	0.50	0.38	0.01	0.02	0.02
D	15.57	15.8	16.1	0.61	0.62	0.63
H1	6.70REF			0.264REF		
e	2.54BSC			0.1BSC		
ØP	3.03	3.18	3.38	0.11	0.12	0.13
L	12.68	12.9	13.2	0.49	0.51	0.52
L1	2.88	3.03	3.18	0.11	0.11	0.12
ØP3	3.15REF			0.124REF		
F3	3.15	3.30	3.45	0.12	0.13	0.13
G3	1.25	1.35	1.55	0.04	0.05	0.06
b1	1.18	1.28	1.43	0.04	0.05	0.05
b2	0.70	0.80	0.95	0.02	0.03	0.03

TO-220MF Part Marking Information



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